

PN EPITAXIAL PLANAR POWER DIODE

CONTACT METALLIZATION

Anode: > 50,000 Å Aluminum

Cathode: Gold

(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL

Size: .220" Diameter (5.59mm)

Thickness: .010" (0.25mm)

BeO PEDESTAL

Size: .175" x .250" (4.45mm x 6.35mm)

Thickness: .028" (0.71mm)

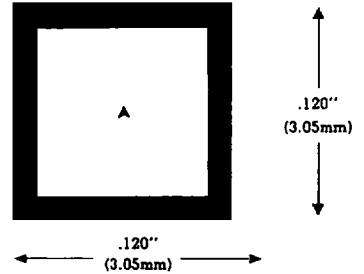
ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the chip be eutectically mounted with gold silicon preform 98/2%.
- b) 18 mil (0.457mm) aluminum wire be ultrasonically attached to the anode contact.

CHIP NUMBER

503



Anode: .106" x .106" (2.69mm x 2.69mm)

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 503 in a DO-4 or equivalent case:

Minimum V_R @ 10 μA	I_R @ 80% V_R	V_F @	I_F	I_F Surge	Maximum t_{RT} @ $I_F = I_R = 1.0A$ $I_{REC} = 0.25A$
> 50V	< 5 μA	1.2V	20A	> 250A	300 ns
> 100V	< 5 μA	1.2V	20A	> 250A	300 ns
> 200V	< 5 μA	1.2V	20A	> 250A	300 ns
> 300V	< 5 μA	1.2V	20A	> 250A	300 ns
> 400V	< 5 μA	1.2V	20A	> 250A	500 ns

TYPICAL DEVICE TYPES: 1N3899, 1N3900, 1N3901, 1N3902
 I_F surge \geq 250A.